

1.2-3.2 GHz 1.2W Power Amplifier

MAAPGM0036-DIE

RO-P-DS-3017 B

Preliminary Information

Features

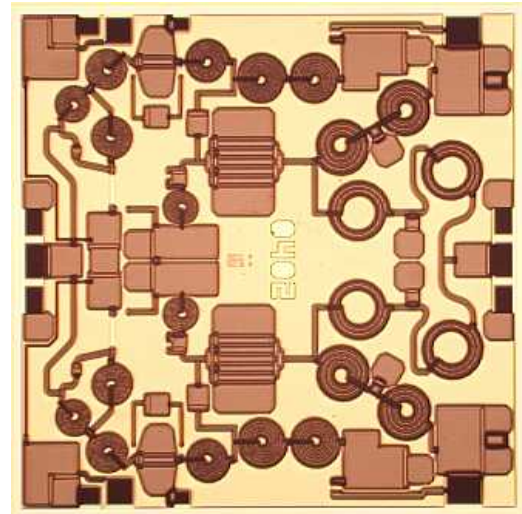
- ◆ 1.2 Watt Saturated Output Power Level
- ◆ Variable Drain Voltage (4-10V) Operation
- ◆ MSAG™ MEFET Process
- ◆ Proven Manufacturability and Reliability
 - No Airbridges
 - Polyimide Scratch Protection
 - No Hydrogen Poisoning Susceptibility

Description

The MAAPGM0036-Die is a 2-stage power amplifier with on-chip bias networks. This product is fully matched to 50 ohms on both the input and output. It can be used as a power amplifier stage or as a driver stage in high power applications.

Fabricated using M/A-COM's repeatable, high performance and highly reliable GaAs Multifunction Self-Aligned Gate MEFET Process, each device is 100% RF tested on wafer to ensure performance compliance.

M/A-COM's MSAG™ process features robust silicon-like manufacturing processes, planar processing of ion implanted transistors, multiple implant capability enabling power, low-noise, switch and digital FETs on a single chip, and polyimide scratch protection for ease of use with automated manufacturing processes. The use of refractory metals and the absence of platinum in the gate metal formulation prevents hydrogen poisoning when employed in hermetic packaging.



Primary Applications

- ◆ 2.5-2.7 GHz MMDS
- ◆ GPS
- ◆ Radar
- ◆ Telemetry

Electrical Characteristics: $T_B = 40^\circ\text{C}^1$, $Z_0 = 50 \Omega$, $V_{DD} = 8\text{V}$, $I_{DQ} \approx 460\text{mA}^2$, $P_{in} = 18 \text{ dBm}$

Parameter	Symbol	Typical	Units
Bandwidth	f	1.2-3.2	GHz
Output Power	POUT	31	dBm
Power Added Efficiency	PAE	30	%
1-dB Compression Point	P1dB	30	dBm
Small Signal Gain	G	20	dB
Input VSWR	VSWR	1.4:1	
Output VSWR	VSWR	1.8:1	
Gate Supply Current	I_{GG}	< 5	mA
Drain Supply Current	I_{DD}	< 725	mA
Output Third Order Intercept	OTOI	40	dBm
3 rd Order Intermodulation Distortion Single Carrier Level = 21 dBm	IM3	-10	dBm
5 th Order Intermodulation Distortion Single Carrier Level = 21 dBm	IM5	-35	dBm
Noise Figure	NF	5	dB
2 nd Harmonic	2f	-12	dBc
3 rd Harmonic	3f	-20	dBc

1. T_B = MMIC Base Temperature
2. Adjust V_{GG} between -2.4 and -1.5V to achieve indicated I_{DQ} .

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Maximum Operating Conditions ³

Parameter	Symbol	Absolute Maximum	Units
Input Power	P _{IN}	23.0	dBm
Drain Supply Voltage	V _{DD}	+12.0	V
Gate Supply Voltage	V _{GG}	-3.0	V
Quiescent Drain Current (No RF, 40% Idss)	I _{DQ}	730	mA
Quiescent DC Power Dissipated (No RF)	P _{DISS}	6.6	W
Junction Temperature	T _J	180	°C
Storage Temperature	T _{STG}	-55 to +150	°C
Die Attach Temperature		310	°C

3. Operation outside of these ranges may reduce product reliability.

Recommended Operating Conditions

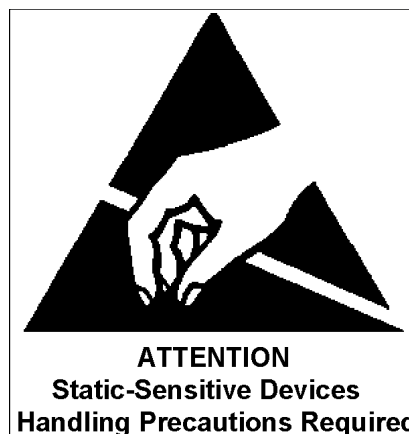
Characteristic	Symbol	Min	Type	Max	Unit
Drain Supply Voltage	V _{DD}	4.0	8.0	10.0	V
Gate Supply Voltage	V _{GG}	-2.4	-2.0	-1.5	V
Input Power	P _{IN}			21.0	dBm
Junction Temperature	T _J			150	°C
Thermal Resistance	θ _{JC}		14.2		°C/W
MMIC Base Temperature	T _B			Note 4	°C

4. Maximum MMIC Base Temperature = 150°C — θ_{JC} * V_{DD} * I_{DQ}

Operating Instructions

This device is static sensitive. Please handle with care. To operate the device, follow these steps.

1. Apply V_{GG} = -2 V, V_{DD} = 0 V.
2. Ramp V_{DD} to desired voltage, typically 8.0 V.
3. Adjust V_{GG} to set I_{DQ}.
4. Set RF input.
5. Power down sequence in reverse. Turn V_{GG} off last.



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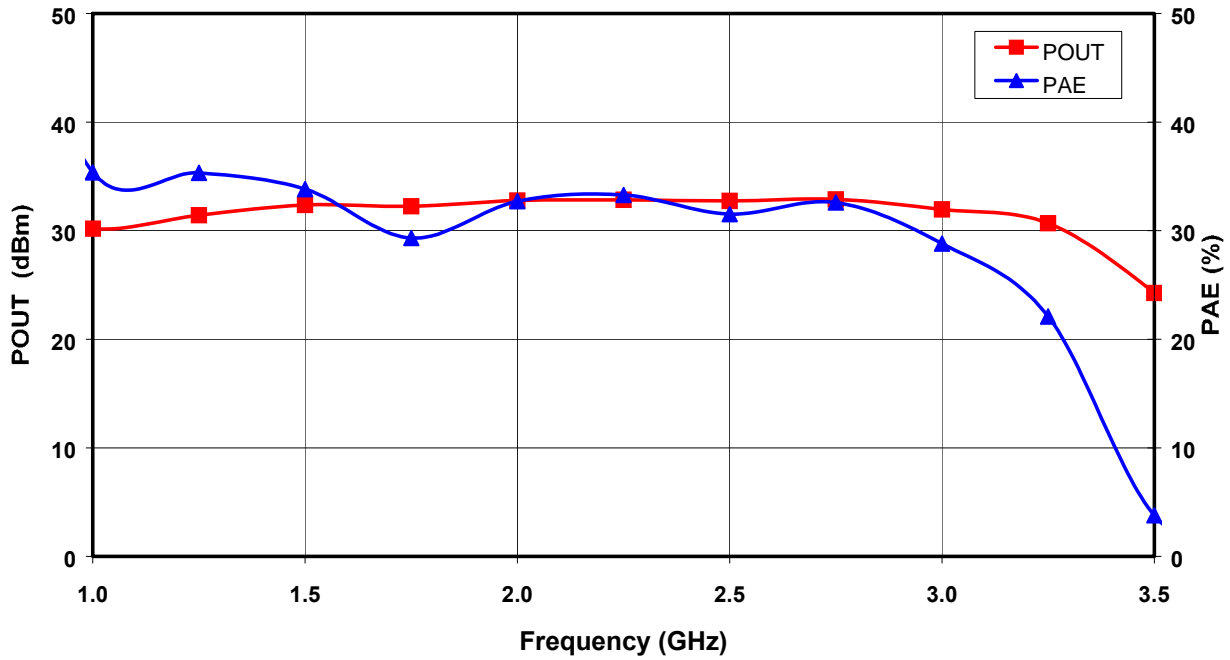


Figure 1. Output Power and Power Added Efficiency vs. Frequency at $V_{DD} = 8V$ and $P_{in} = 18$ dBm.

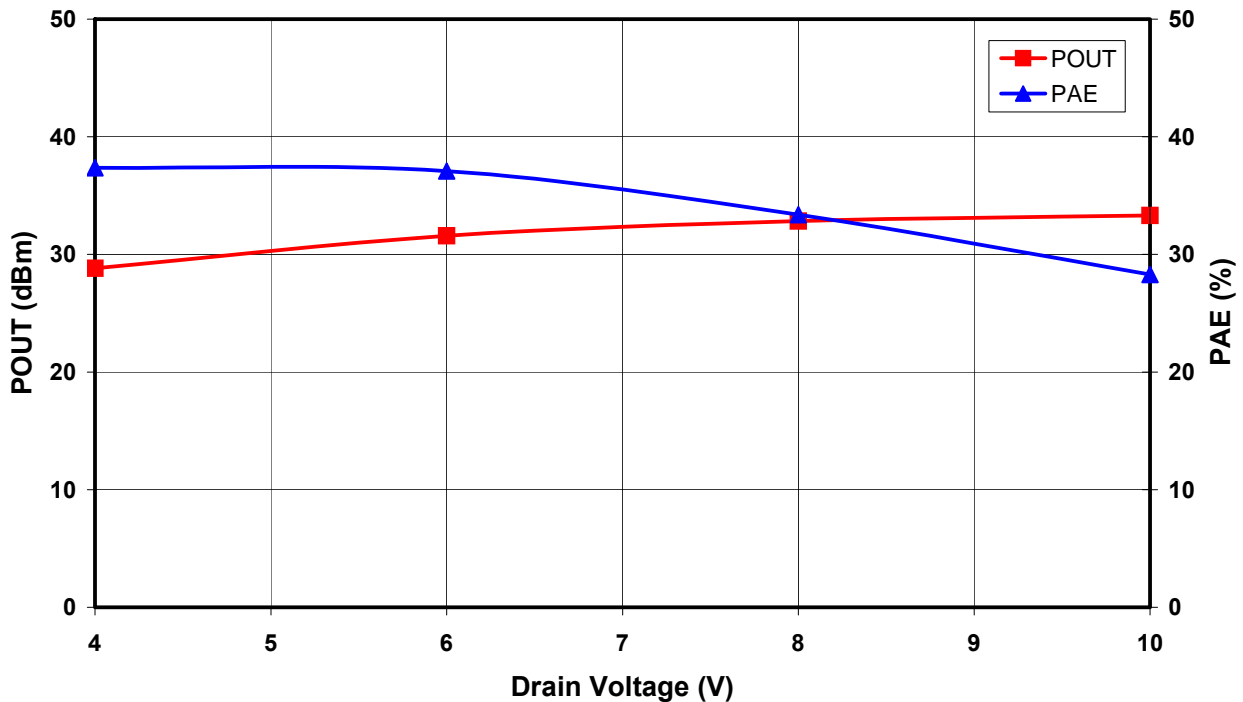


Figure 2. Saturated Output Power and Power Added Efficiency vs. Drain Voltage at $f_o = 2.25$ GHz.

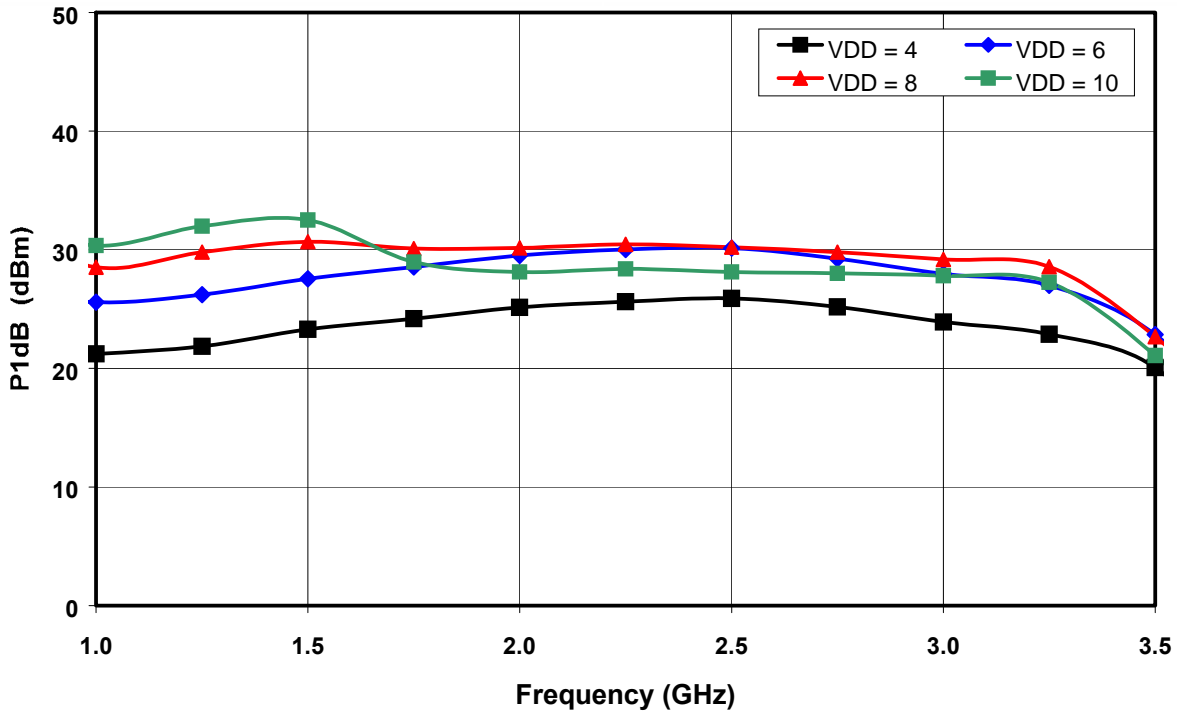


Figure 3. 1dB Compression Point vs. Drain Voltage

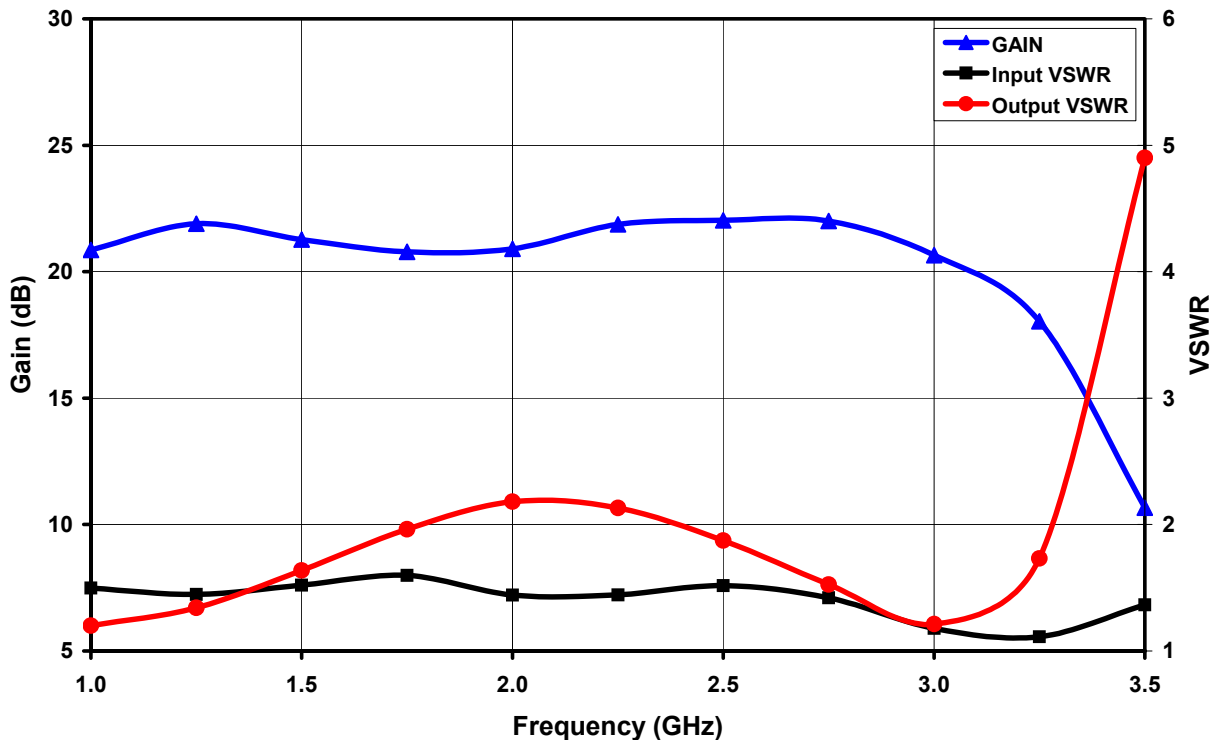
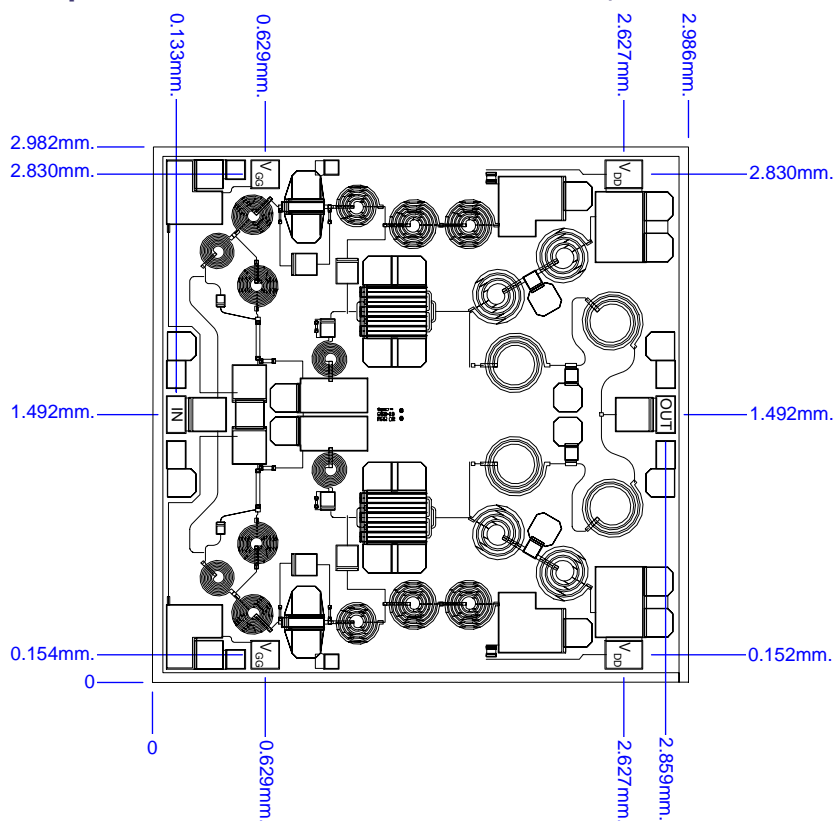


Figure 4. Small Signal and VSWR vs Frequency at VDD = 8V.

Mechanical Information

Chip Size: 2.986 x 2.982 x 0.075 mm (118 x 117 x 3 mils)



Chip edge to bond pad dimensions are shown to the center of the bond pad.

Figure 5. Die Layout

Bond Pad Dimensions

Pad	Size (μm)	Size (mils)
RF In and Out	100 x 200	4 x 8
DC Drain Supply Voltage VDD	200 x 150	8 x 6
DC Gate Supply Voltage VGG	150 x 150	6 x 6

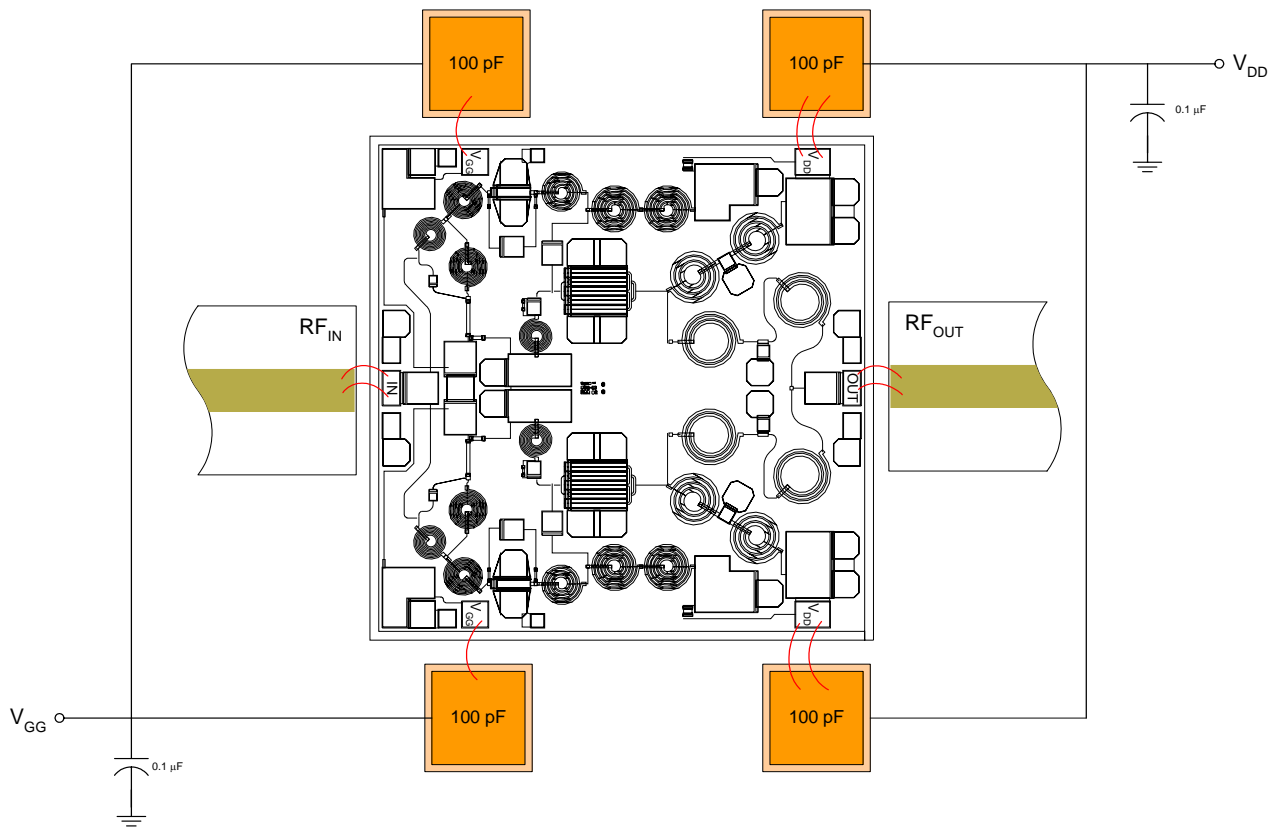


Figure 6. Recommended bonding diagram for pedestal mount.
Support circuitry typical of MMIC characterization fixture for CW test-

Assembly Instructions:

Die attach: Use AuSn (80/20) 1-2 mil. preform solder. Limit time @ 300 °C to less than 5 minutes.

Wirebonding: Bond @ 160 °C using standard ball or thermal compression wedge bond techniques. For DC pad connections, use either ball or wedge bonds. For best RF performance, use wedge bonds of shortest length, although ball bonds are also acceptable.

Biasing Note: Must apply negative bias to V_{GG} before applying positive bias to V_{DD} to prevent damage to amplifier.